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Solutions

- 1. Advantanges: Fast process
 - Can be done in bulk
 - Anisotropic etching allows for selectivity

Disadvantages: - Saftey hazards and waste that comes from using chemicals

- Undercutting and over etching
- Chemicals require temperature regulations
- 2.

t = 22/60 = .367 minutes.

 $1.6 * 0.367 = .587 \mu m$

vertical depth = $.587 \mu m$

horizontal depth $= .587 \, \mu m$. Isotropic processes etch the same rate in both the horizontal and vertical direction.

3.

The mask has a length of 15um. In order to get a 5um deep v-groove, the mask width must be $2*(5\text{um/tan}(54.7^\circ)) = 7.1\text{um}$. Since the depth is 5um, the time for etching is (1min/um)*(5um) = 5 minutes.

4.

Materials with different crystal orientations can be used to prevent an etch from continuing in a particular direction.

Boron etch stop: as regions of silicon become very heavily-doped (\sim 6x10¹⁹ cm⁻³), etch rates for common etchants drop dramatically.

Photolithography can provide enough energy to change the chemical structure of a layer such as photoresist. An etchant can then be selected which removes exposed or unexposed portions of material.